

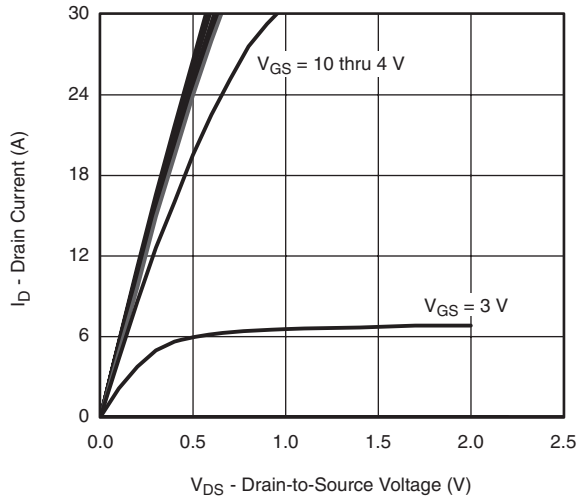
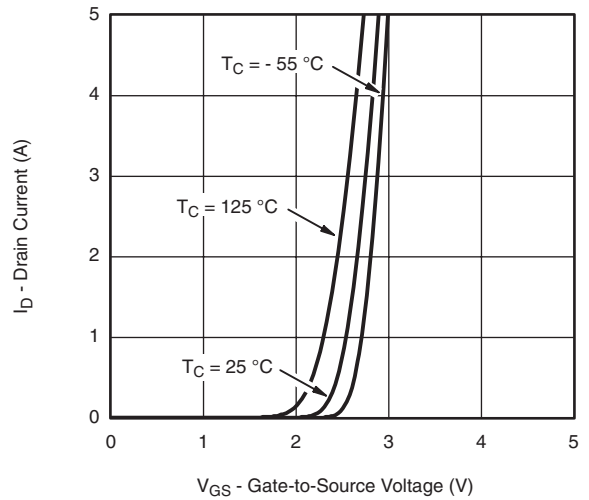
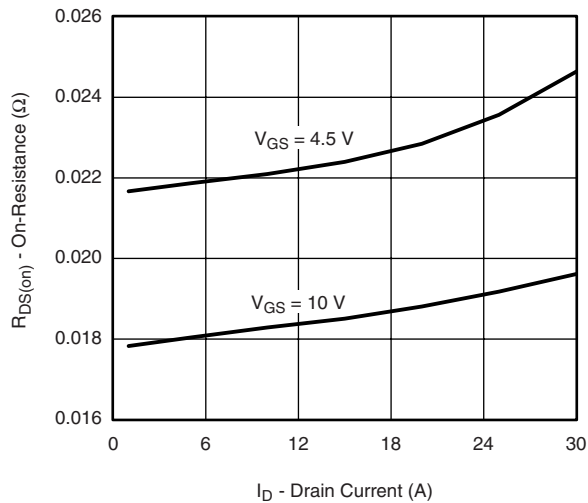
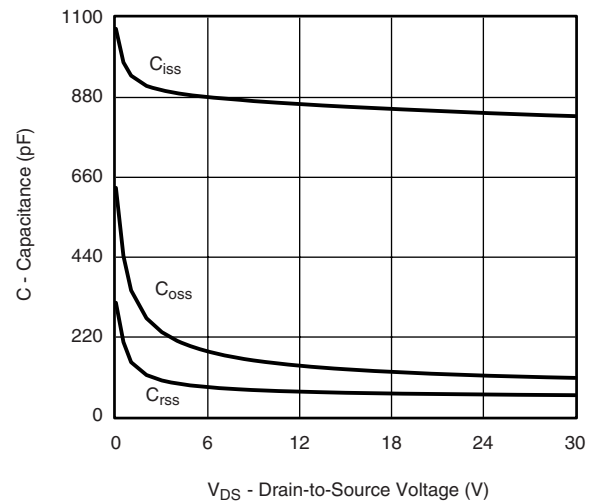
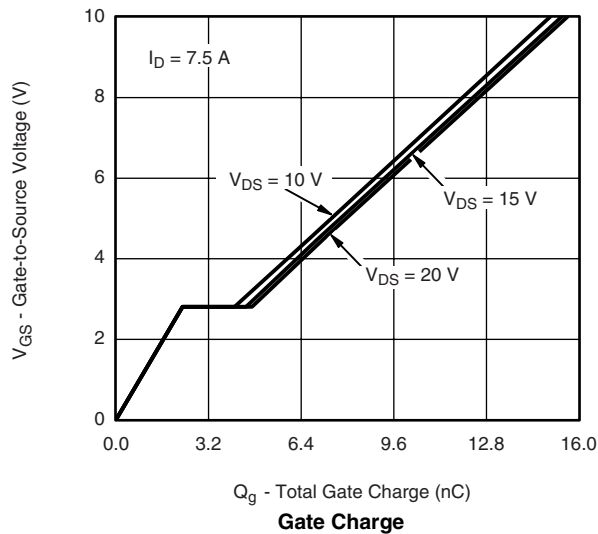
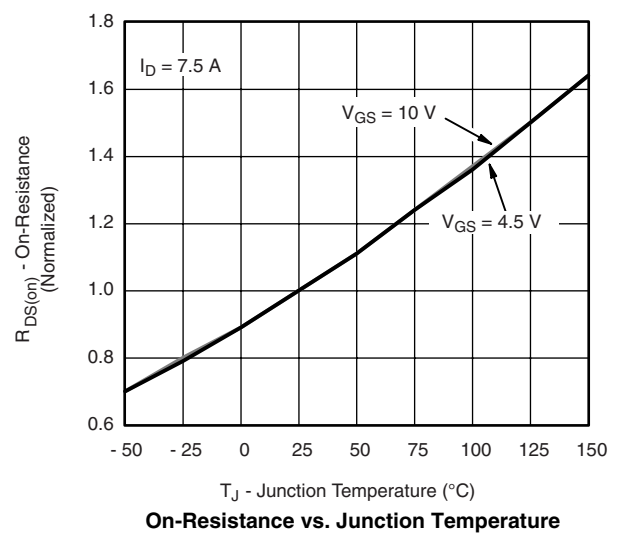
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		31		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.1		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2		2.4	V
Gate Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	20			A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 7.5 A		0.018	0.022	Ω
		V _{GS} = 4.5 V, I _D = 6.5 A		0.022	0.027	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7.5 A		20		S
Dynamic ^a						
Input Capacitance	C _{iss}	N-Channel V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		865		pF
Output Capacitance	C _{oss}			131		
Reverse Transfer Capacitance	C _{rss}			66		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 7.5 A		15.4	23	nC
		N-Channel V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 7.5 A		7	10.5	
Gate-Source Charge	Q _{gs}			2.3		
Gate-Drain Charge	Q _{gd}			2.2		
Gate Resistance	R _g	f = 1 MHz	0.4	1.9	3.8	Ω
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω		9	18	ns
Rise Time	t _r			12	24	
Turn-Off Delay Time	t _{d(off)}			17	34	
Fall Time	t _f			9	18	
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		17	34	
Rise Time	t _r			13	26	
Turn-Off Delay Time	t _{d(off)}			19	35	
Fall Time	t _f			9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			2.4	A
Pulse Diode Forward Current ^a	I _{SM}				30	
Body Diode Voltage	V _{SD}	I _S = 1.8 A		0.77	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	N-Channel I _F = 5 A, dl/dt = 100 A/μs, T _J = 25 °C		16	32	ns
Body Diode Reverse Recovery Charge	Q _{rr}			8	16	nC
Reverse Recovery Fall Time	t _a			10		ns
Reverse Recovery Rise Time	t _b			6		

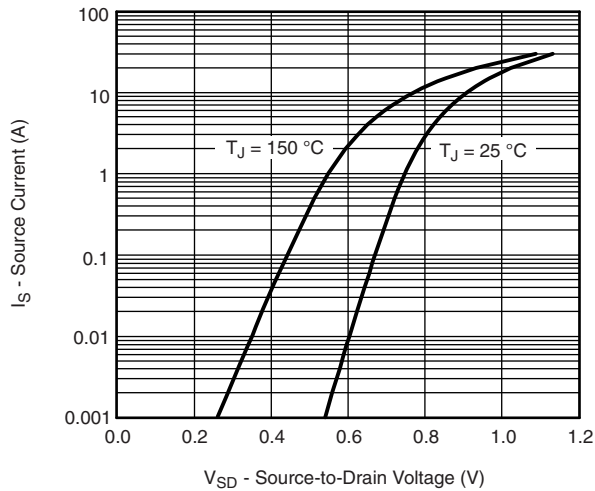
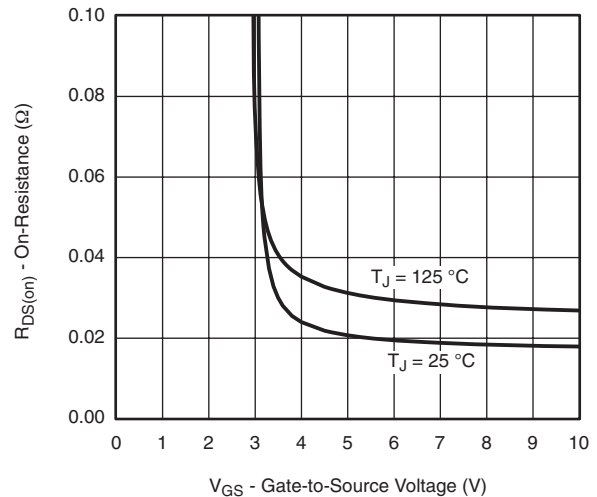
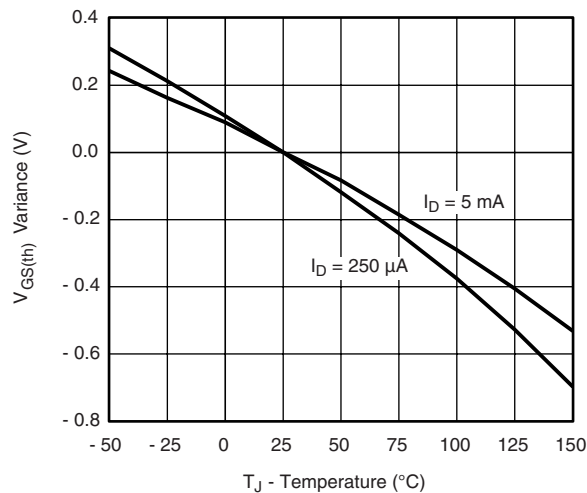
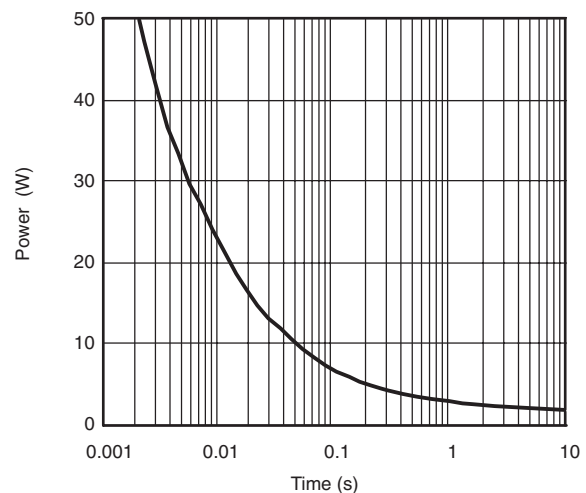
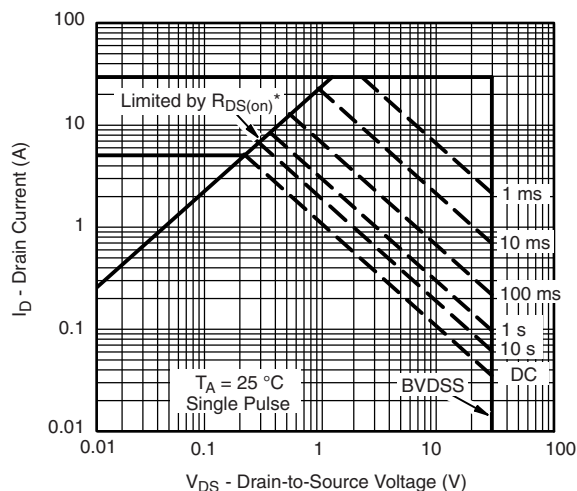
Notes:

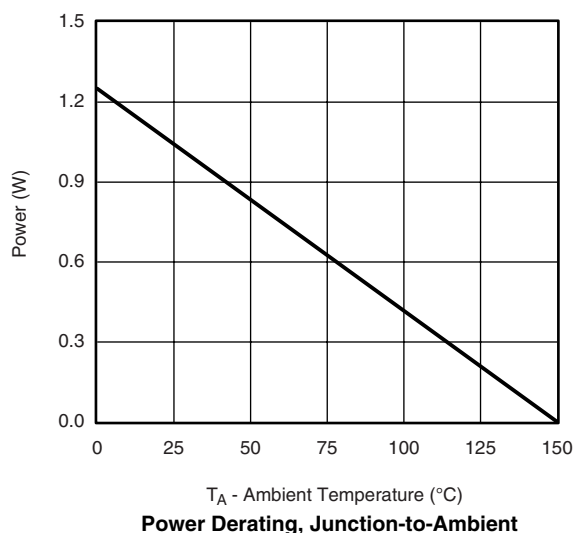
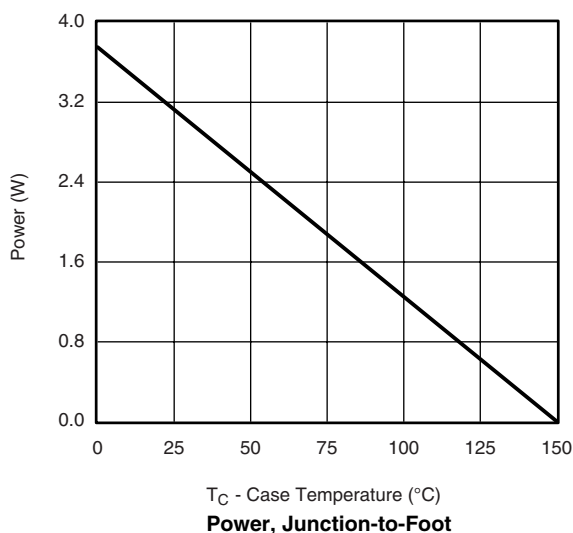
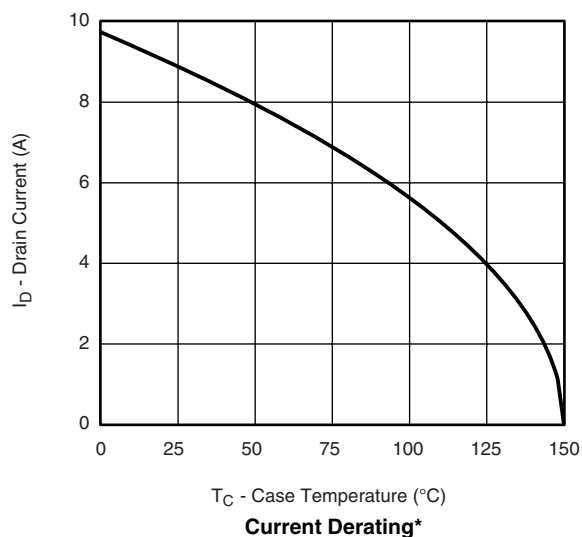
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

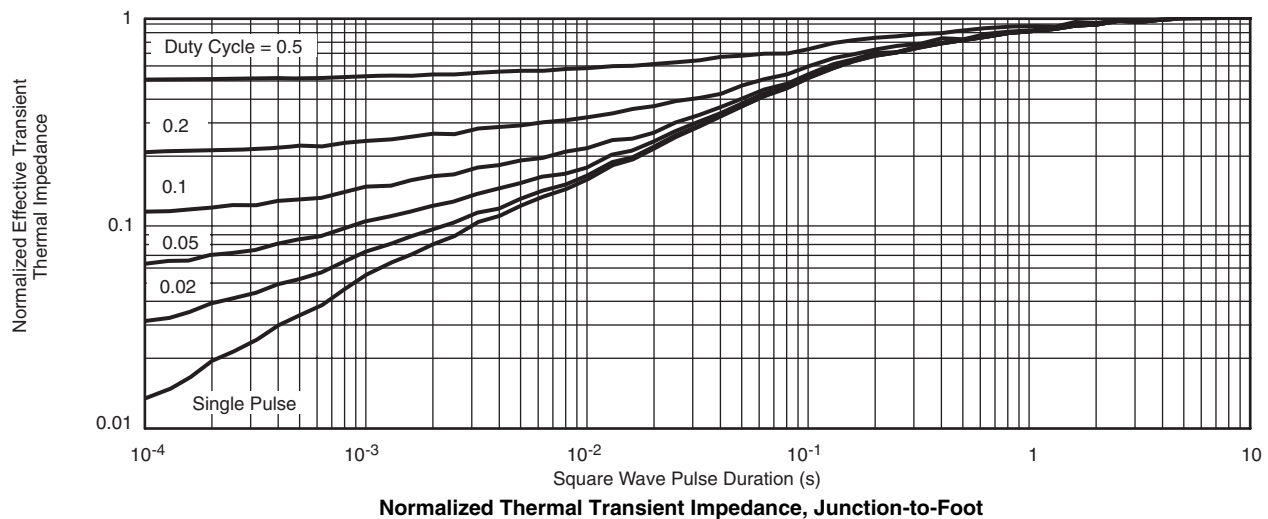
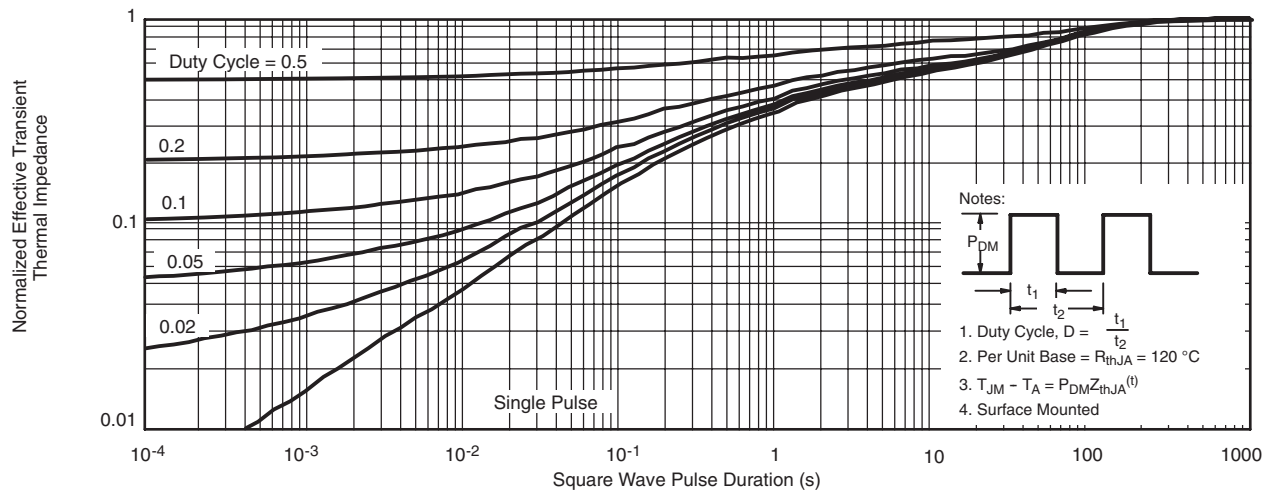
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**

**MOSFET TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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